



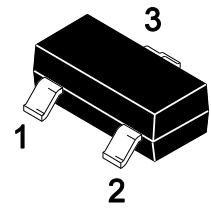
1SS181⁺

Silicon Epitaxial Planar Switching Diode

Features

- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

Package

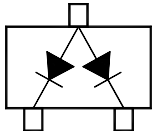


1.Cathode1 2.Cathode2
3.Anode1、 Anode2

Marking Code : A1

Electrical Symbol

3.Anode1、 Anode2



1.Cathode1 2.Cathode2

Maximum Ratings (at T_J = 25°C)

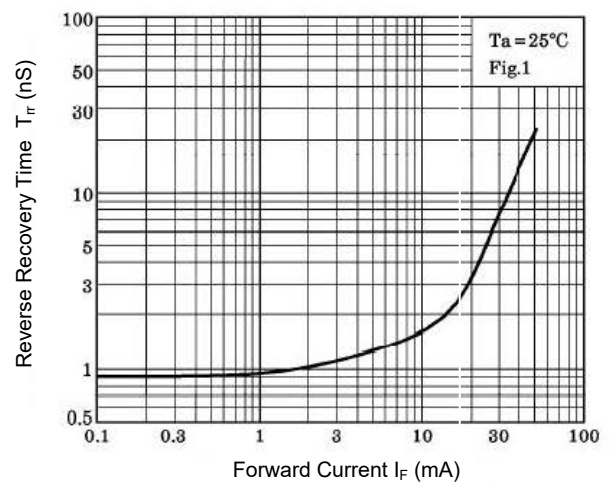
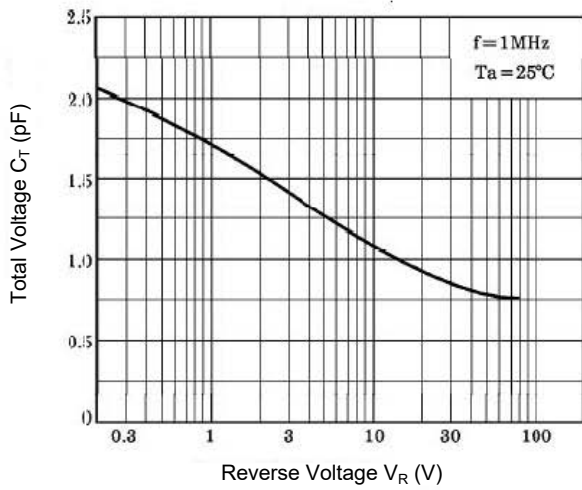
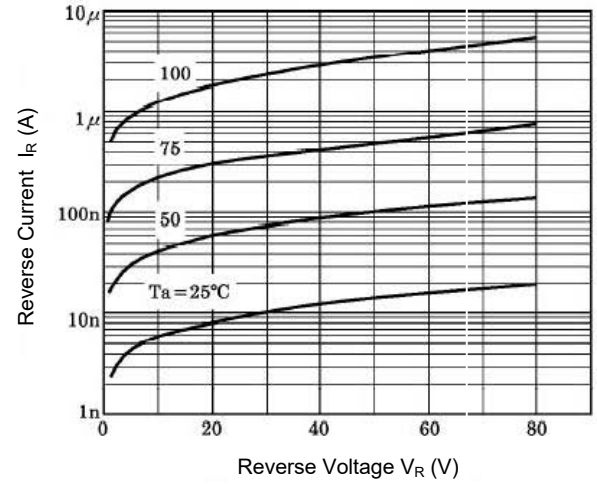
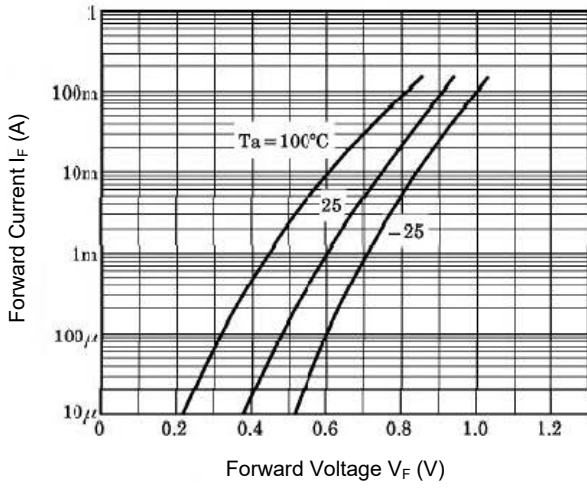
Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V _{RRM}	85	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Non-Repetitive Peak Forward Surge Current (10 ms)	I _{FSM}	2	A
Maximum Power Dissipation	P _D	350	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Electrical Characteristics (at T_J = 25°C)

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at V _R = 30 V at V _R = 80 V	I _R	0.1 0.5	μA
Typical Junction Capacitance at V _R = 0 V, f = 1 MHz	C _j	4	pF
Maximum Reverse Recovery Time at I _F = 10 mA	T _{rr}	4	nS



Typical Characteristic Curves





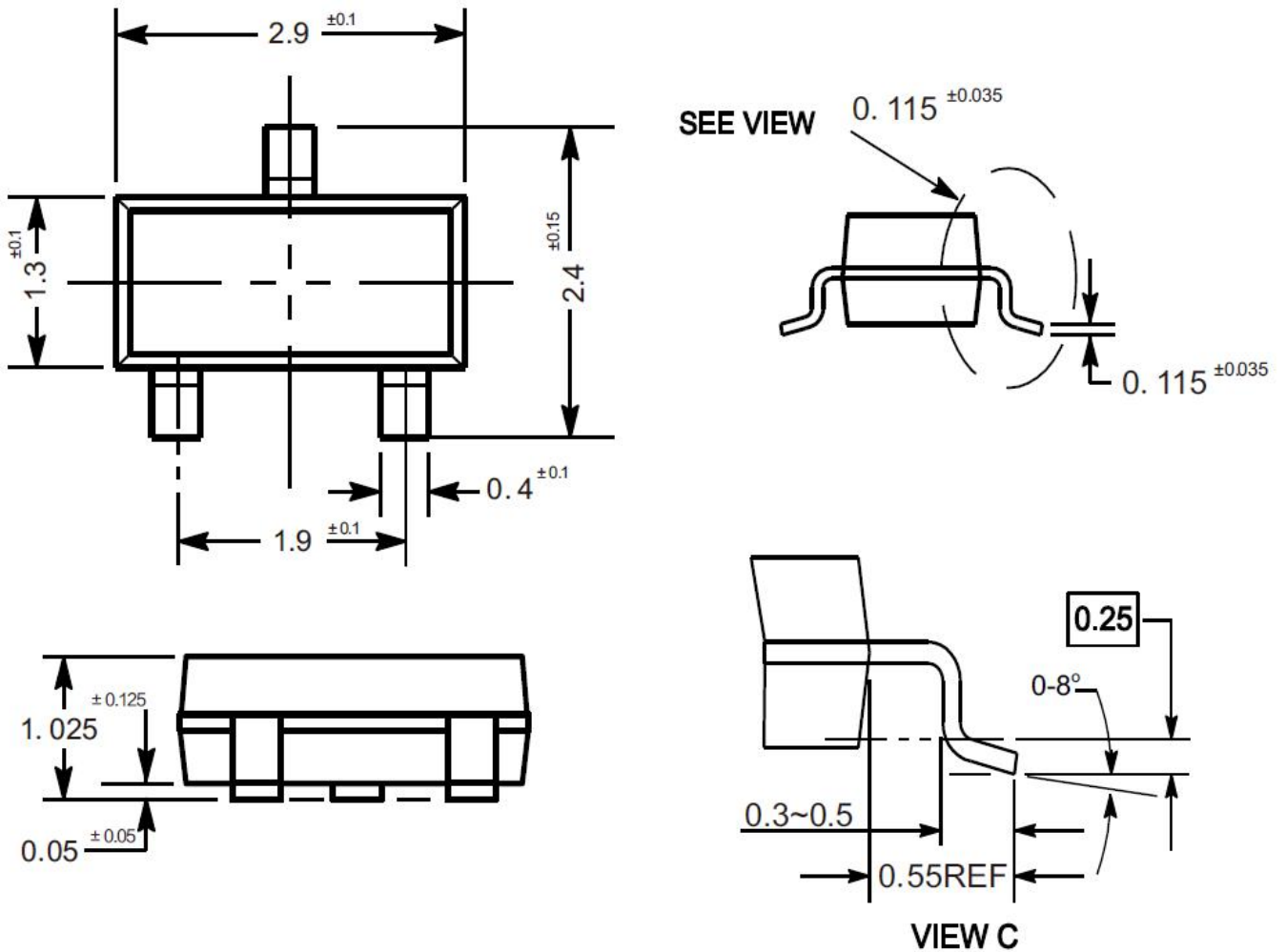
1SS181⁺

Silicon Epitaxial Planar Switching Diode

Package Outline

SOT-23

Dimensions in mm



Ordering Information

Device	Package	Shipping
1SS181	SOT-23	3,000PCS/Reel&7inches